



10N60Z

Power MOSFET

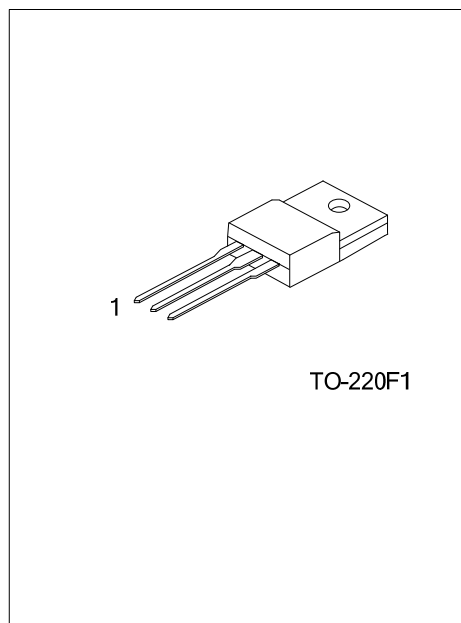
10A, 600V N-CHANNEL POWER MOSFET

DESCRIPTION

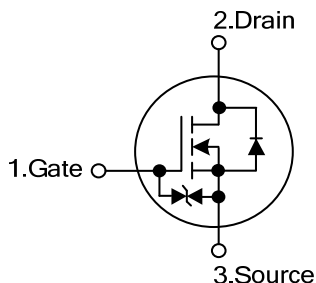
The **UTC 10N60Z** is a high voltage and high current power MOSFET, designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and have a high rugged avalanche characteristics. This power MOSFET is usually used at high speed switching applications in power supplies, PWM motor controls, high efficient DC to DC converters and bridge circuits.

FEATURES

- * $R_{DS(ON)} = 0.75\Omega @ V_{GS} = 10V$
- * Low gate charge (typical 44nC)
- * Low C_{RSS} (typical 18 pF)
- * Fast switching
- * 100% avalanche tested
- * Improved dv/dt capability



SYMBOL



ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
10N60ZL-TF1-T	10N60ZG-TF1-T	TO-220F1	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>10N60ZL-TF1-T</p> <p>(1)Packing Type</p> <p>(2)Package Type</p> <p>(3)Lead Free</p>	<p>(1) T: Tube</p> <p>(2) TF1: TO-220F1</p> <p>(3) L: Lead Free, G: Halogen Free</p>
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■ ABSOLUTE MAXIMUM RATINGS ($T_C=25^\circ\text{C}$ unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Drain-Source Voltage	V_{DSS}	600	V
Gate-Source Voltage	V_{GSS}	± 20	V
Avalanche Current (Note 2)	I_{AR}	10	A
Drain Current	Continuous	I_D	10
	Pulsed (Note 2)	I_{DM}	38
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	530
	Repetitive (Note 2)	E_{AR}	15.6
Peak Diode Recovery dv/dt (Note 4)	dv/dt	4.5	V/ns
Power Dissipation	P_D	50	W
Junction Temperature	T_J	+150	$^\circ\text{C}$
Operating Temperature	T_{OPR}	-55 ~ +150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature

3. $L = 14.2\text{mH}$, $I_{AS} = 10\text{A}$, $V_{DD} = 50\text{V}$, $R_G = 25\ \Omega$ Starting $T_J = 25^\circ\text{C}$

4. $I_{SD} \leq 9.5\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$

■ THERMAL DATA

PARAMETER	SYMBOL	RATING	UNIT
Junction to Ambient	θ_{JA}	62.5	$^\circ\text{C}/\text{W}$
Junction to Case	θ_{JC}	2.5	$^\circ\text{C}/\text{W}$

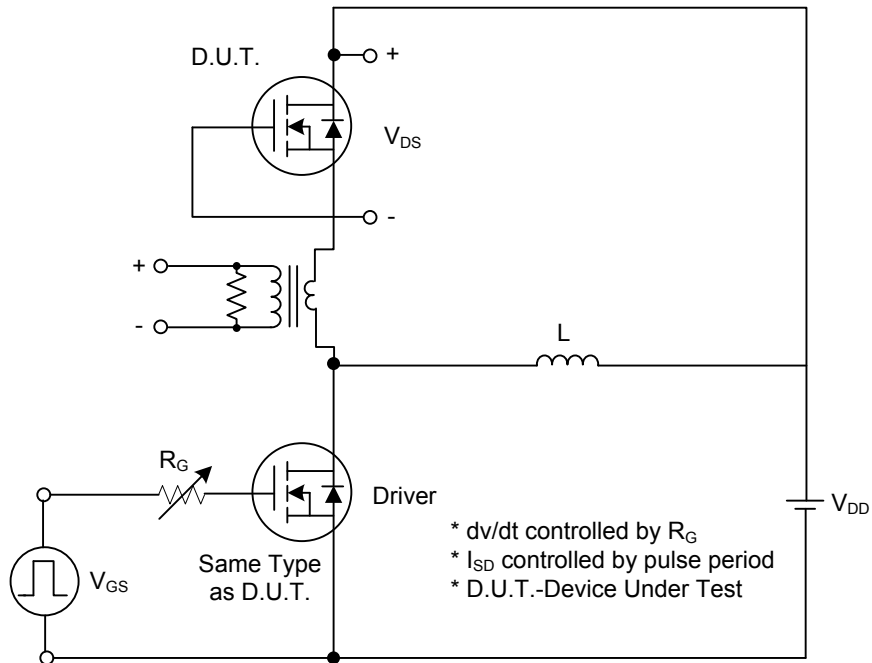
■ ELECTRICAL CHARACTERISTICS(T_C=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250μA	600			V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =600V, V _{GS} =0V			1	μA
Gate-Source Leakage Current	Forward	I _{GSS} V _{GS} =20 V, V _{DS} =0V			5	μA
	Reverse		V _{GS} =-20 V, V _{DS} =0V			-5
Breakdown Voltage Temperature Coefficient	ΔBV _{DSS} /ΔT _J	I _D =250μA, Referenced to 25°C		0.7		V/°C
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} =V _{GS} , I _D =250μA	2.0		4.0	V
Static Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =5A		0.68	0.75	Ω
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{ISS}	V _{DS} =25V, V _{GS} =0V, f=1.0 MHz		1570	2040	pF
Output Capacitance	C _{OSS}			166	215	pF
Reverse Transfer Capacitance	C _{RSS}			18	24	pF
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	t _{D(ON)}	V _{DS} =300V, I _D =10A, R _G =25Ω (Note 1, 2)		23	55	ns
Turn-On Rise Time	t _R			69	150	ns
Turn-Off Delay Time	t _{D(OFF)}			144	300	ns
Turn-Off Fall Time	t _F			77	165	ns
Total Gate Charge	Q _G	V _{DS} =480V, I _D =10A, V _{GS} =10 V (Note 1, 2)		44	57	nC
Gate-Source Charge	Q _{GS}			6.7		nC
Gate-Drain Charge	Q _{GD}			18.5		nC
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Drain-Source Diode Forward Voltage	V _{SD}	V _{GS} =0 V, I _S =10A			1.4	V
Maximum Continuous Drain-Source Diode Forward Current	I _S				10	A
Maximum Pulsed Drain-Source Diode Forward Current	I _{SM}				38	A
Reverse Recovery Time	t _{rr}	V _{GS} =0 V, I _S =10A, dI _F /dt=100A/μs (Note 1)		420		ns
Reverse Recovery Charge	Q _{RR}				4.2	

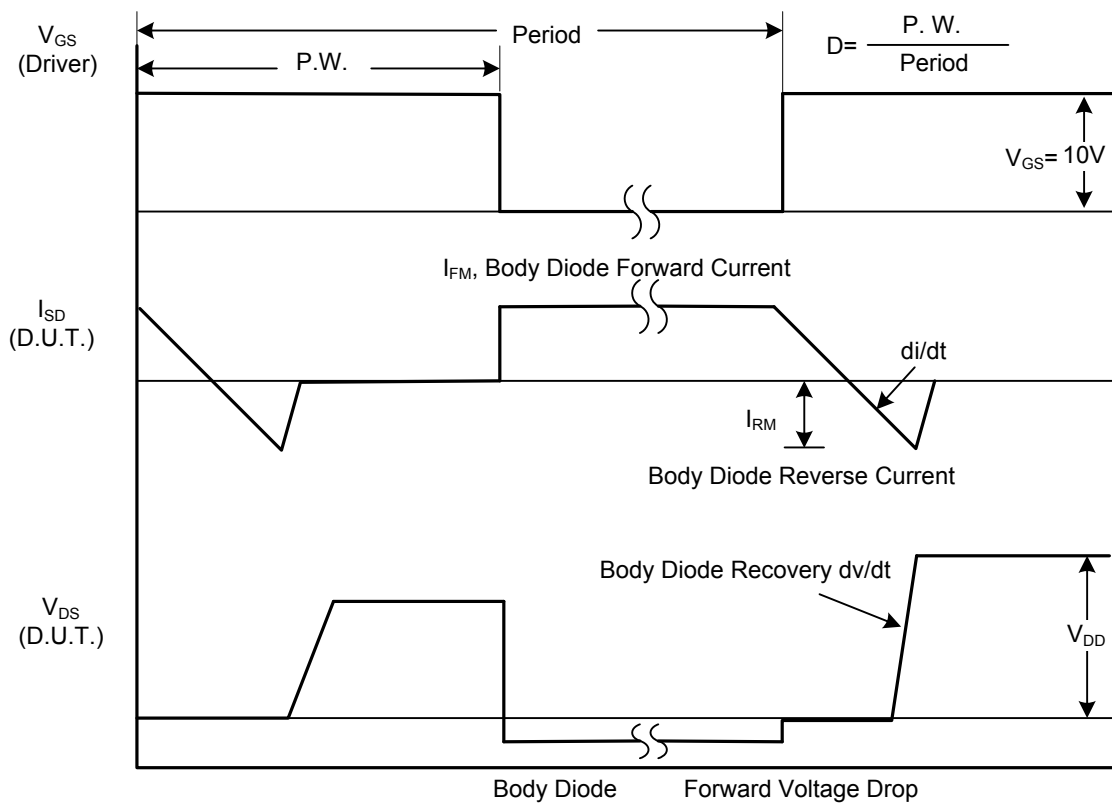
Notes: 1. Pulse Test : Pulse width ≤300μs, Duty cycle ≤2%

2. Essentially independent of operating temperature

■ TEST CIRCUITS AND WAVEFORMS

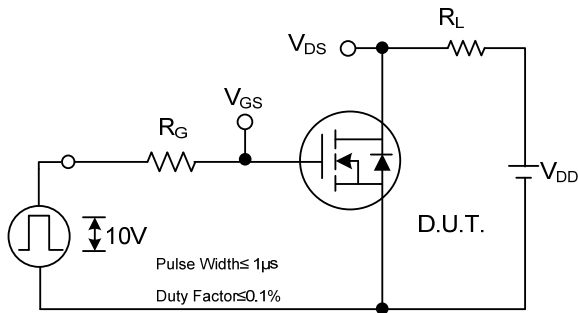


Peak Diode Recovery dv/dt Test Circuit

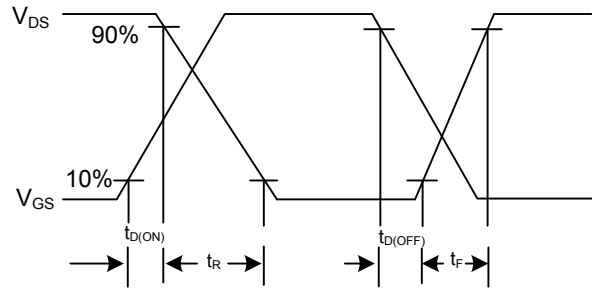


Peak Diode Recovery dv/dt Waveforms

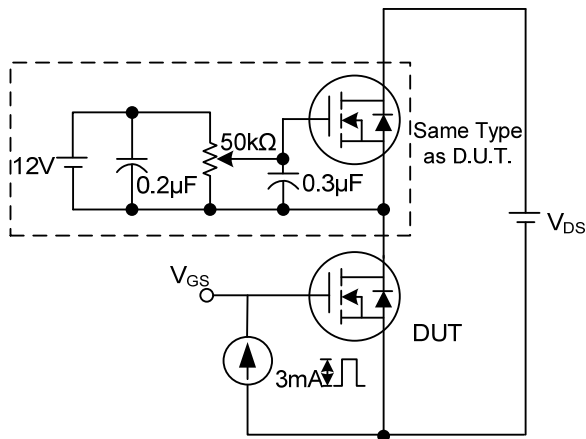
TEST CIRCUITS AND WAVEFORMS (Cont.)



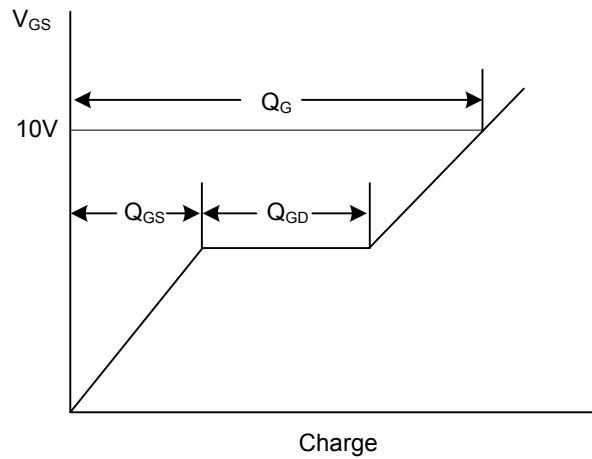
Switching Test Circuit



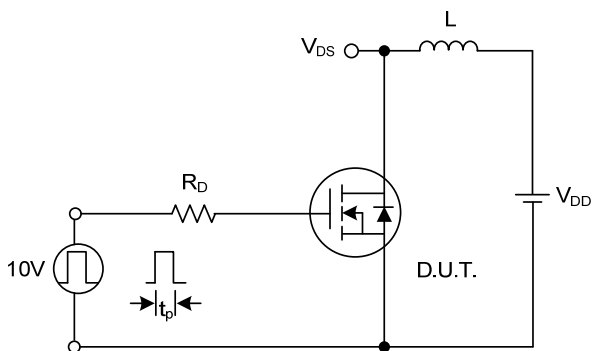
Switching Waveforms



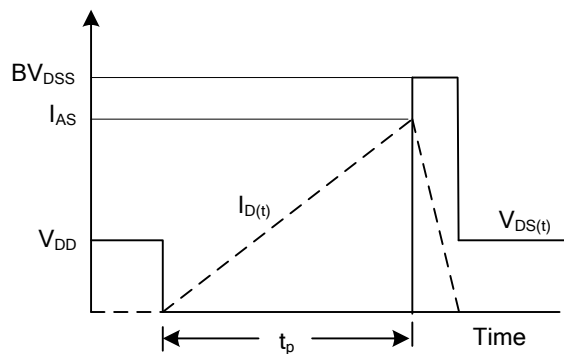
Gate Charge Test Circuit



Gate Charge Waveform



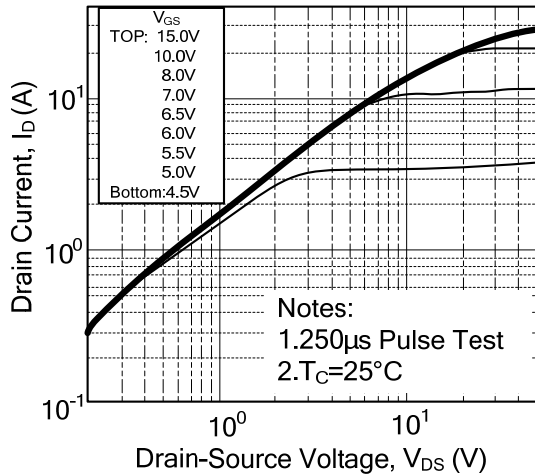
Unclamped Inductive Switching Test Circuit



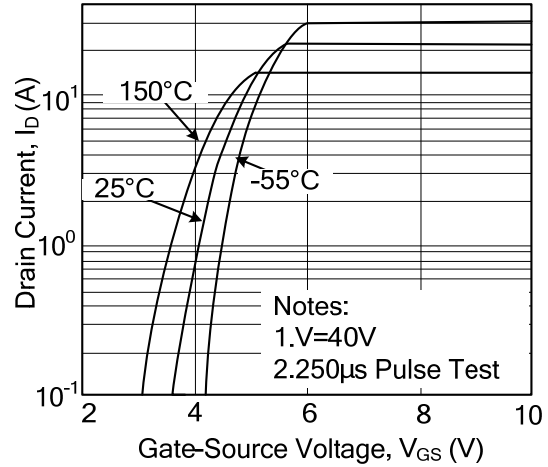
Unclamped Inductive Switching Waveforms

TYPICAL CHARACTERISTICS

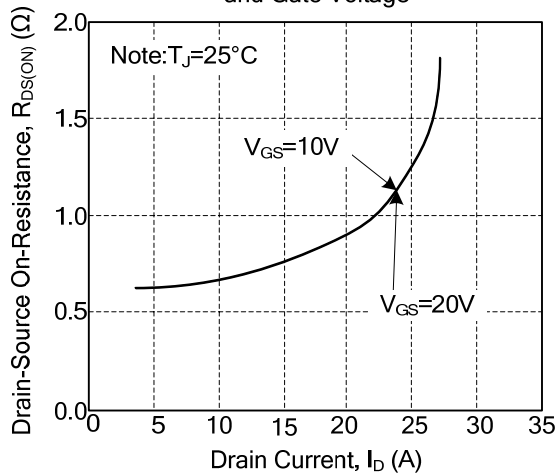
On-Region Characteristics



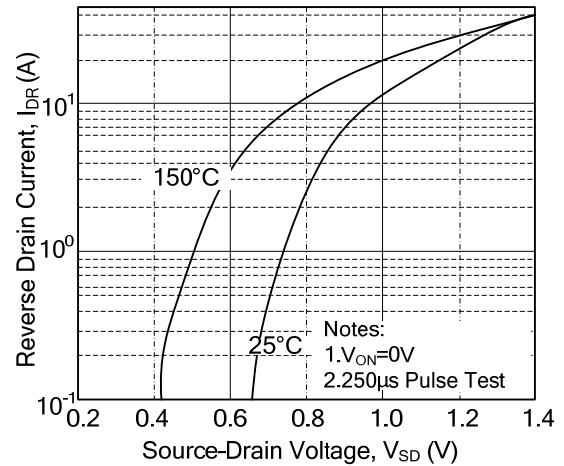
Transfer Characteristics



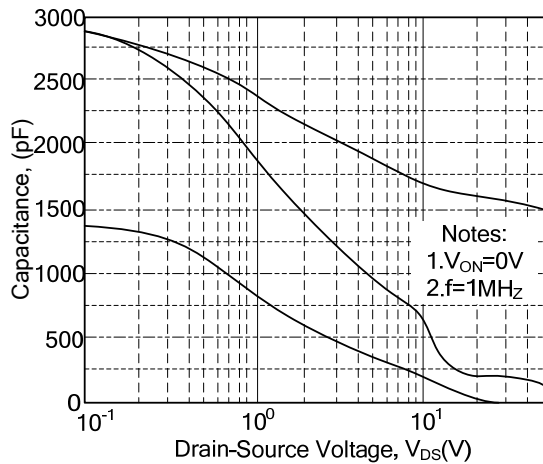
On-Resistance Variation vs. Drain Current and Gate Voltage



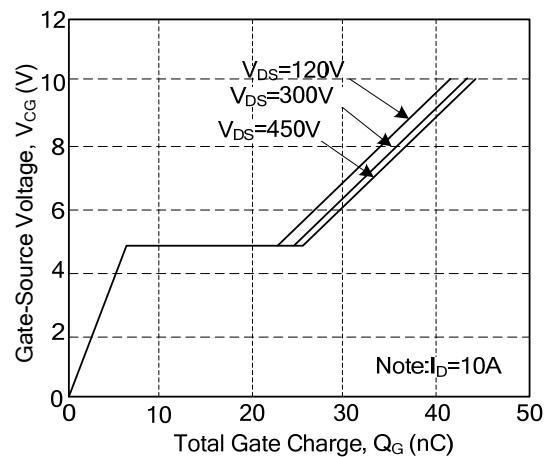
Body Diode Forward Voltage Variation with Source Current and Temperature



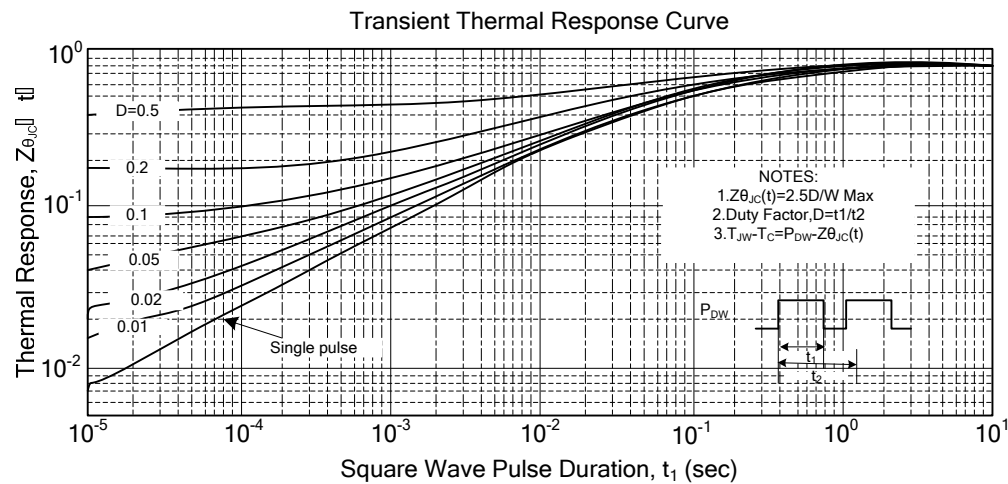
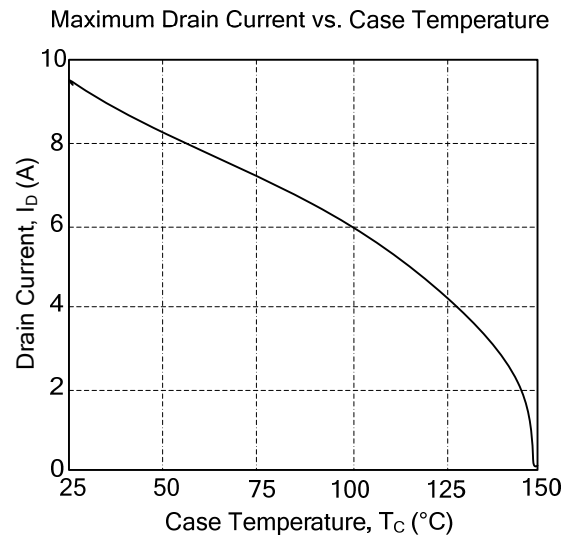
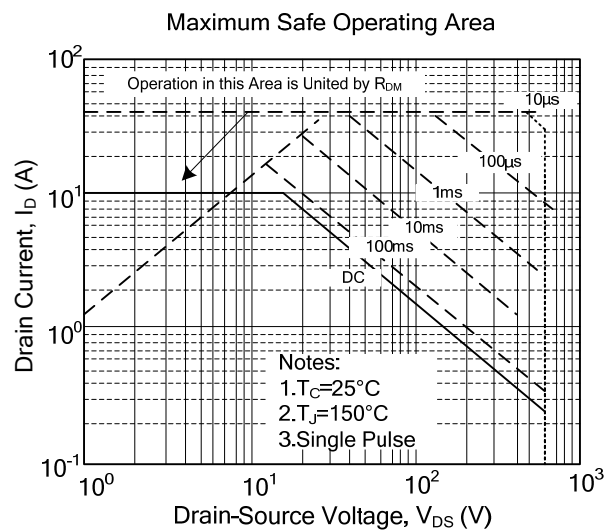
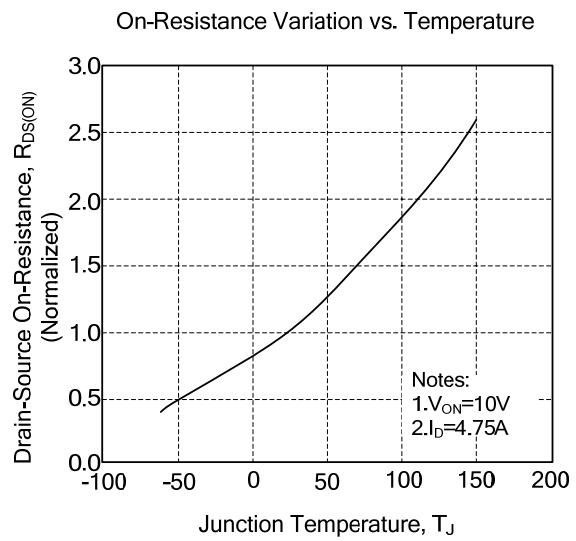
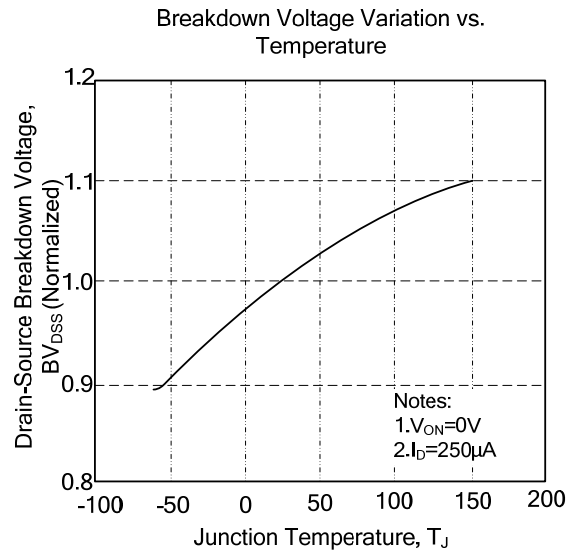
Capacitance Characteristics



Gate Charge Characteristics



■ TYPICAL CHARACTERISTICS(Cont.)



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